L Number	Hits		DB	Time stame
-	1515	1 3 - 0 Hear 100 (recessive droops) Hear 100	USPAT:	Time stamp 2003/12/03 18:14
		Substrate	US-PGPUB	2003/12/03 18:14
-	119		USPAT;	2002/20/02 20 2
	!	substrate) and ((silicon near3 germanium)	US-PGPUB	2003/12/03 18:14
		S1?Ge Si-Ge SiGe)	US-PGPUB	
-	24755	((silicon near3 germanium) Si?Ge Si-Ge SiGe)	USPAT;	2002/25/25
		J = 1 00 5100)		2003/12/03 18:14
-	8216	gate near100 (reces\$4 groov\$3 open\$4 trench)	US-PGPUB	0000/20/20
		near100 substrate .	USPAT;	2003/12/03 18:14
-	1,9782		US-PGPUB	2000 (200 (200 )
	·	same substrate	USPAT;	2003/12/03 18:15
-	8237	gate with (reces\$4 groov\$3 open\$4 trench)	US-PGPUB	
l i		with substrate	USPAT;	2003/12/03 18:15
-	19782		US-PGPUB	
		trench) near100 substrate) (gate same	USPAT;	2003/12/03 18:15
		(reces\$4 groov\$3 open\$4 trench) same	US-PGPUB	
		substrate) (gate with (reces\$4 groov\$3		
		open\$4 trench) with substrate)		
-	1619	(((silicon near3 germanium) Si?Ge Si-Ge	,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	
		SiGe)) and ((gate near100 (reces\$4 groov\$3	USPAT;	2003/12/03 18:16
		open\$4 trench) near100 substrate) (gate same	US-PGPUB	
		(reces\$4 groov\$3 open\$4 trench) same		
*		substrate) (gate with (reces\$4 groov\$3		
		open\$4 trench) with substrate))		
-	4	(("6214679") or ("5624869") or ("5883003")	,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	
		or ("6037922")).PN.	USPAT;	2003/12/04 10:03
-	45	"6214679"	US-PGPUB	1
		"5624869"	USPAT;	2003/12/04 10:03
		"5883003 <sup>1</sup> "	US-PGPUB	
		"6037922"		
-	1623	(((silicon near3 germanium) Si?Ge Si-Ge	USPAT;	2222 /2 - / -
		Side)) and ((gate near100 (recest) groups)	US-PGPUB	2003/12/04 10:22
		open\$4 trench) near100 substrate) (gate game	US-PGPUB	
		(recess4 groovs3 opens4 trench) came		
		Substrate) (gate with (recess4 groows?		
		open\$4 trench) with substrate))		
	i			
- 1	38	(((silicon near3 germanium) Si?Ge Si-Ge	EPO; JPO;	2002/12/04 10 05
	1	Side)) and ((gate nearing (recest) groups	DERWENT;	2003/12/04 10:23
	1	open\$4 trench) near100 substrate) (gate game	IBM_TDB	
l	1	(IECES\$4 GroovS3 open\$4 trench) same		1
		Substrate) (gate with (recess4 groovs)		
		open\$4 trench) with substrate))		1
_				
	653	anisotropic\$6 near100 etch\$3 near100	EPO; JPO;	2003/12/04 11:20
1	1	(substrate wafer) near100 gate	DERWENT;	
.	. 0	(and and the second sec	IBM_TDB	
	١	(anisotropic\$6 near100 etch\$3 near100	EPO; JPO;	2003/12/04 11:19
		(substrate wafer) near100 gate) and	DERWENT;	
		((silicon near3 germanium) Si-Ge Si?Ge SiGe)	IBM TDB	
		· · · · · · · · · · · · · · · · · · ·		